



# Stanford University

## **Stanford University Power Electronics Research - Laboratory**

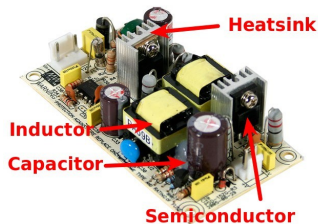
### **Power Electronics in the SUPER-Lab**

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# Power density in Converters



- ▶ Inductors and capacitors
  - ▶  $\text{size} \propto \frac{1}{f_s}$
  - ▶ Slow improvements in size and performance
- ▶ Semiconductors
  - ▶ Switching loss  $\propto f_s$
  - ▶ Great advances in recent years
- ▶ Heatsink: Hard to extract heat from small volumes



$$\begin{aligned} f_P &= 72\text{kHz} \\ \rho &= 4.5\text{ kW/dm}^3 \end{aligned}$$



$$\begin{aligned} &250\text{ kHz} \\ \rho &= 10\text{ kW/dm}^3 \end{aligned}$$



$$\begin{aligned} &500\text{ kHz} \\ \rho &= 13\text{ kW/dm}^3 \end{aligned}$$



$$\begin{aligned} &1\text{ MHz} \\ \rho &= 14\text{ kW/dm}^3 \end{aligned}$$

Fig. 18. Dependency of the power density of a unidirectional three-phase/level PFC rectifier system (Vienna Rectifier) on the switching frequency. Only for the system with  $f_P=72\text{kHz}$  the heatsink volume is considered in the given power density figure ( $4.5\text{ kW/dm}^3$  and/or  $74\text{ W/in}^3$ ); accordingly the systems with  $f_P=250 / 500 / 1000\text{kHz}$  actually show a lower power density, i.e. a power density limit of  $\rho \approx 10\text{ kW/dm}^3$  could be assumed for  $f_P=1\text{ MHz}$ .

Kolar, J.W.; Biela, J.; Waffler, S.; Friedli, T.; Badstuebner, U., "Performance trends and limitations of power electronic systems," *CIPS, 2010 6th Int. Conf.*, vol., no., pp.1,20, 16-18 March 2010

# Power density trends

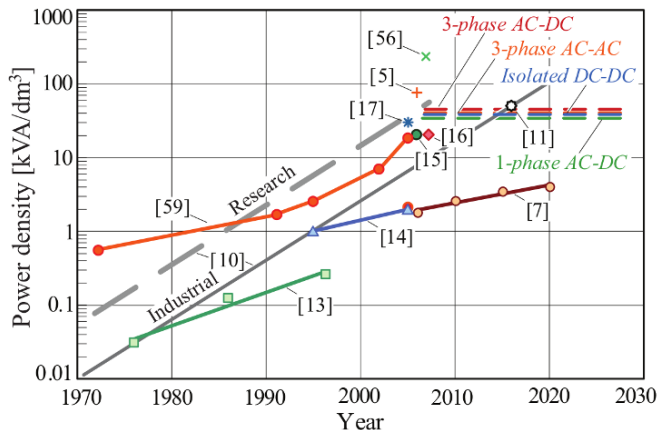


Fig. 2. Power Density trend of industrial and research systems<sup>(10)</sup> and the Power Density Barriers.

*J.W. Kolar, U. Drofenik, J. Biela, M.L. Heldwein, H. Ertl, T. Friedli and R.D. Simon, "PWM Converter Power Density Barrier", IEEE Transactions on Industry Applications (Section D), Volume: 128-D, Issue: 4, April 2008.*

# Very High Frequency Power Electronics

## Switching at 10's of MHz

- ▶ High frequency operation reduces the energy storage requirements of inductors and capacitors.
- ▶ Inductors are small enough to be fabricated with an air-core

## Use PCB to implement inductors

- ▶ Inductances and capacitances can be implemented within the PCB
- ▶ Filters and EMI shielding can also be implemented within the PCB.

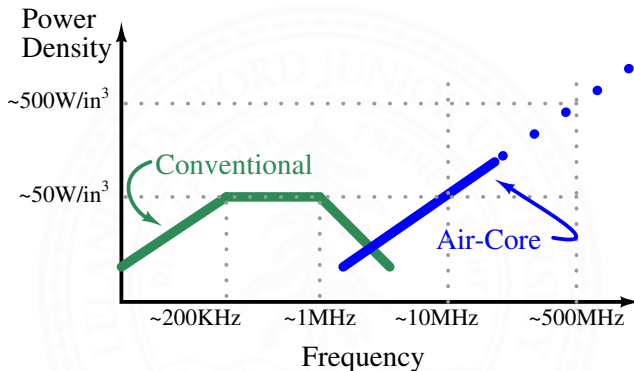
## New Circuit Topologies

Implement rectifiers that reduce switch stress allowing for higher overall gains.

- ▶ Use better switches with lower parasitics



# Why switching at 10s of MHz?

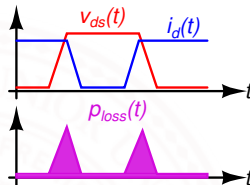
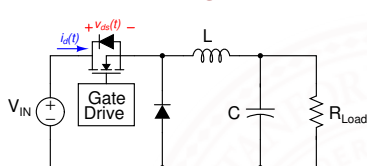


## The promise of VHF power conversion

Reduced energy storage → Smaller passive components & Faster transient response

*J. S. Glaser, et al, "A 900W, 300V to 50V dc-dc power converter with a 30 MHz switching frequency," In Proc. Twenty-Fourth Annual IEEE Applied Power Electronics Conf. and Exposition APEC 2009, pp. 1121-1128, 2009.*

# Device Switching Loss



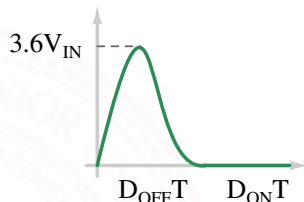
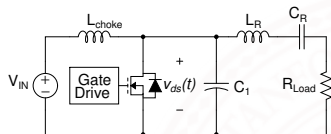
## Switching loss (hard switching)

- ▶ V-I overlap during device switching
- ▶ Includes device charge removal at turn off (device recovery)
- ▶ Includes device capacitance discharge at turn on
  - ▶ Energy stored at turn off, discharged at turn on (if not ZVS)

## Loss dependency

- ▶ Proportional to switching frequency
- ▶ Some components increase with load current, some independent
- ▶ Increase as device area increases

# Soft Switching Operation



Resonant Zero-Voltage Switching reduces switching loss (e.g., Class E)

- ▶ V-I overlap loss greatly reduced via capacitive snubbing
- ▶ ZVS turn-on avoids capacitive energy dump

Strategy is effective, but

- ▶ Only efficient over a narrow load range
- ▶ Control becomes challenging at very high frequencies
- ▶ Device stresses are high for many topologies
  - ▶ increased conduction loss

# Magnetic Losses

## Conventional cored magnetics

- ▶ Core loss increases rapidly with frequency ( $\propto f^k$ )
- ▶ Good core materials become scarce above 10 MHz
- ▶ An optimum frequency range exists for cored inductors

At high enough frequencies, the inductor values needed are small

- ▶ Build entirely coreless designs
- ▶ Air-core components not subject to Curie temperature limitations

## Core-less magnetics

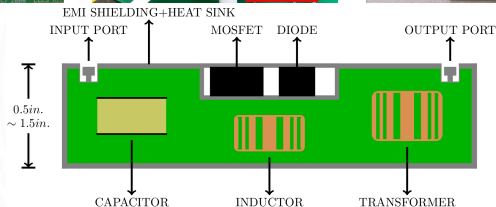
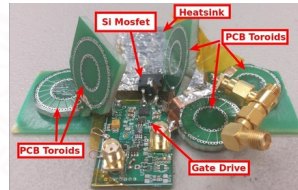
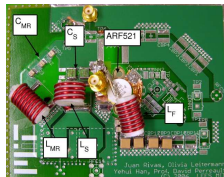
- ▶ Get better as frequency increases
- ▶ Easier to integrate
- ▶ Can be made self shielding in some cases

# Air-core inductors for VHF converters



- ▶ Air-core components not subject to saturation or Curie temperature limitations
- ▶ Toroidal are an improvements over solenoids as the magnetic field is constrained to the torus
  - ▶ Lower stray fields → Lower EMI issues
- ▶ PCB toroids have better copper coverage and lower loss and very repeatable
- ▶ Better air-core passives are possible with new fabrication techniques: 3D-printing

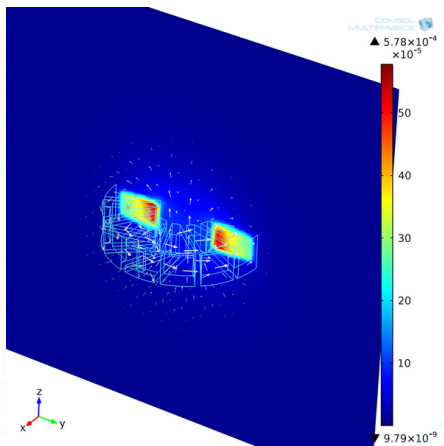
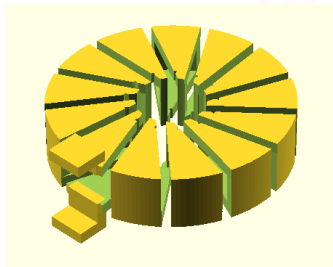
# Path forward



Replacing solenoids with toroids → Printing passives within inner layers of PCB.

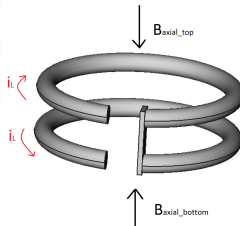
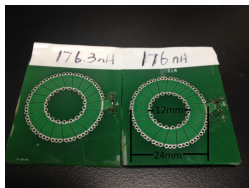
- ▶ Top and bottom layers function as EMI shield and heatsink
- ▶ Planar-stackable structure

# “one turn” inductance



- ▶ one turn axial direction inductance that can lead to EMI, extra losses on the ground plane
- ▶ Also results in current crowding on the inner ring of the toroid
- ▶ For air core inductors, the “one turn” inductance is comparable in value to the toroidal value

# “one turn” inductance cancellation



- We can place two inductors with same dimensions but opposite winding direction vertically stacked to cancel the axial fields.



## Capacitor Implementation: dielectric loss

- ▶ Capacitors in the converter experiences high frequency (27.12 MHz) and high voltage swing(e.g. greater than 500 V)
- ▶ Low “loss tangent” is the key to select dielectric material

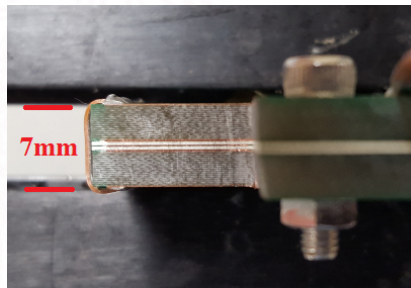
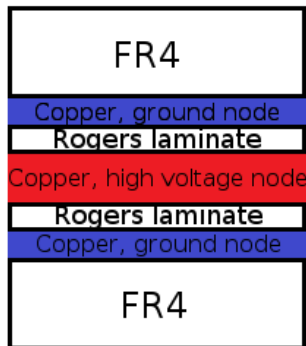
	FR4	Rogers 4360G2
$\epsilon_r$	4.5	6.15
$\tan\delta$	0.018	0.0038

- ▶ For example, for a capacitor with  $20\text{mm} \times 20\text{mm}$ , 0.3mm thickness, and  $300\text{ V}_{RMS}$ ,

$$P_{loss,FR4} = V_{RMS}^2 \times \frac{\omega\epsilon_0\epsilon_r\tan\delta A}{d} = 6.4W$$

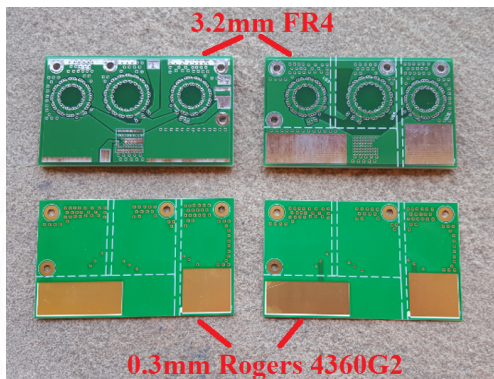
$$P_{loss,Rogers4360} = V_{RMS}^2 \times \frac{\omega\epsilon_0\epsilon_r\tan\delta A}{d} = 1.8W$$

# Capacitor Implementation



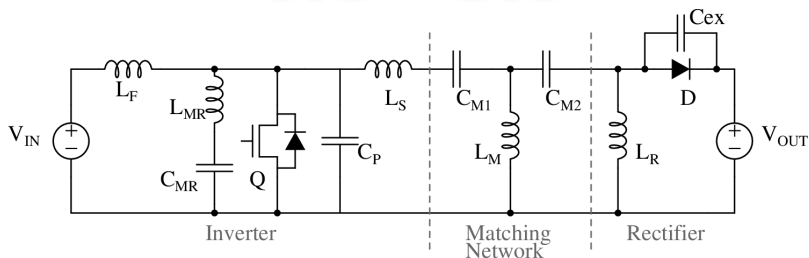
- To minimize dielectric loss, we avoid having high voltage node and ground node through FR4

# PCB implementation



- ▶ FR4 and Rogers laminates used for inductors and capacitors respectively. They are mechanically holed together to form a stack
  - ▶ Rogers laminates was limited to capacitor implementation due to cost considerations
  - ▶ Rogers has much better electrical and thermal characteristics

# Dc-dc Converter



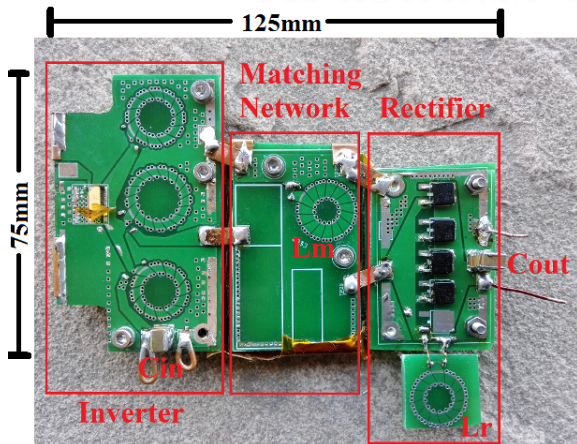
- ▶ Inverter, matching network, rectifier stage
- ▶ The matching network is chosen such that no dc block is necessary in the inverter stage
- ▶ All inductors and capacitors are resonant and feasible to implement in PCB

# Bill of Material

Part	Value	Description
$L_F$	105 nH	$2 \times 52.5$ nH PCB inductor (Q=85@27.12MHz)
$L_{MR}$	105 nH	$2 \times 52.5$ nH PCB inductor (Q=85@27.12MHz)
$L_S$	180 nH	$2 \times 90$ nH PCB inductor (Q=90@27.12MHz)
$L_M$	67 nH	$2 \times 134$ nH PCB inductor (Q=94@27.12MHz)
$L_R$	81 nH	$1 \times 81$ nH PCB inductor (Q=100@27.12MHz)
$C_{MR}$	82 pF	0.3 mm Rogers 4360G2
$C_P$	160 pF	0.3 mm Rogers 4360G2
$C_{M1}$	235 pF	0.254 mm Rogers 6010.2LM
$C_{M1}$	436 pF	0.254 mm Rogers 6010.2LM
$C_{IN}$	3 $\mu$ F	X7R capacitor
$C_{OUT}$	6 $\mu$ F	X7R capacitor
MOSFET	GS66508T	650 V GaN FET
Diode	STPSC4H065B-TR	650 V SiC shottky diodes

- PCB implementation greatly simplifies the tuning and improves repeatability
- Input and output filter capacitors implemented with SMD device.
- Multi-resonant structure are currently under investigation to reduce capacitor size to some extent

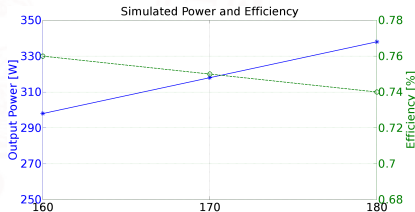
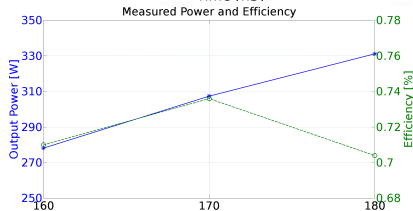
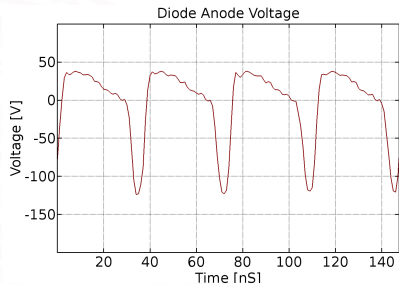
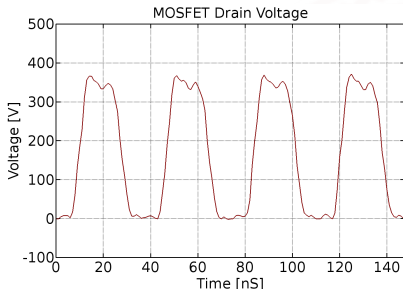
# Prototype Implementation



## Specs

$V_{IN}$	170V
$V_{OUT}$	28V
$P_{OUT}$	320W
$\eta$	73.6 %

# Prototype waveforms



# 3D printed passive components



(a) 3D CAD model



(b) 3D printed plastic mold



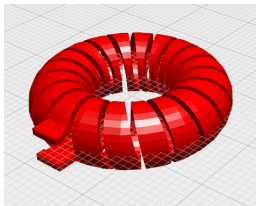
(c) cast silver model

Fig.: Steps in the fabrication of a 3D inductor. (a) shows the OpenJSCAD model, (b) shows a translucent plastic model and (c) shows a sterling silver inductor. The 3D inductor has 10nH inductance and its dimensions are OD=18mm, ID=6mm, N=4. Also notice the rounded cross section.

- ▶ 3D printing can overcome limitations of PCB and wire-wound inductors
- ▶ Overhangs, curved surfaces, texture possible



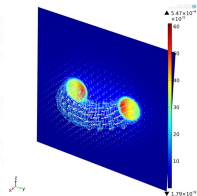
# Preliminary designs (Circular Cross Section)



(a) CAD

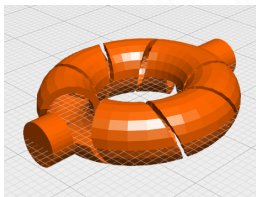


(b) Cast



(c) FEM

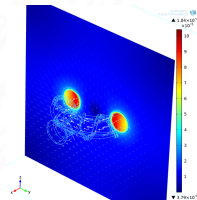
Fig.: toroid inductor with a round cross section. OD=29mm, ID=11mm, N=20.



(a) CAD



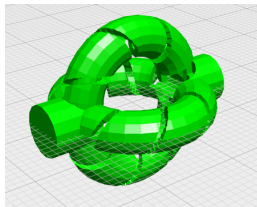
(b) Cast



(c) FEM

Fig.: Toroid inductor with a round cross section and two parallel windings. OD=28mm, ID=13mm, N=4.

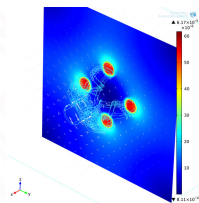
# Preliminary designs



(a) CAD

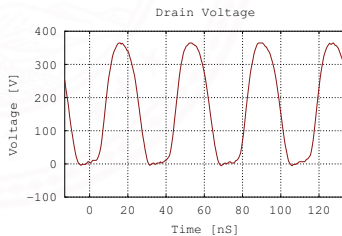
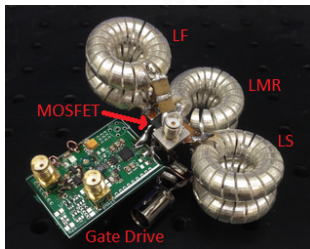


(b) Cast

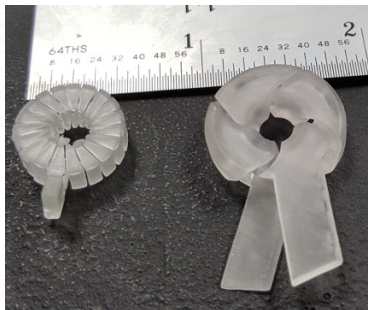
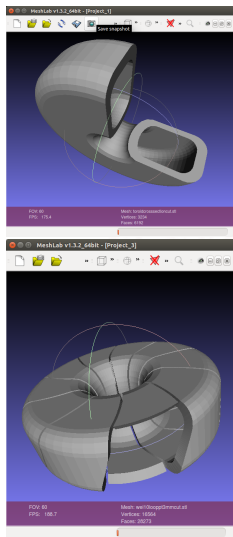


(c) FEM

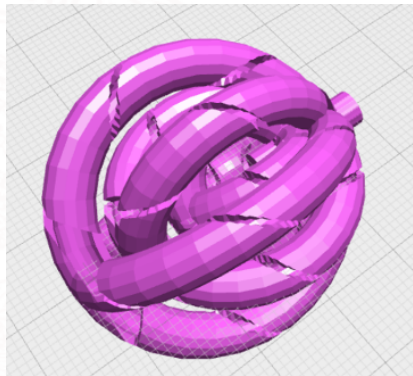
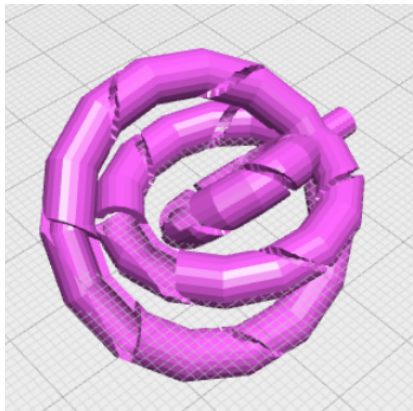
Fig.: Toroid inductor with a round cross section and four parallel windings. OD=21mm, ID=10mm, N=4.



# 3D printed inductor with optimal cross-sections

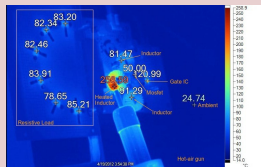


## 3D printed converters



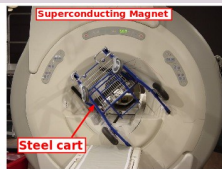
# Harsh environment operation

## Operation at high temperature



- ▶ Air-core inductors don't saturate or have Curie temperature limitation
- ▶ WBG high-temp semiconductors will enable new applications
  - ▶ Power converters in engines, catalytic converter

## Operation an large magnetic fields



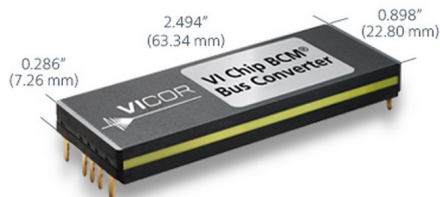
- ▶ Conventional converters not MRI friendly
- ▶ Ferromagnetic components saturate
- ▶ Air-cored converters can operate inside magnet
  - ▶ Harmonics miss imaging bands

# Good progress made in low voltage power electronics

VICOR 400 V to 50 V dc-dc

## Low Voltage Power Conversion

- ▶ Focus on moderate gain ratio step down
  - ▶ Efficient, power dense converters commercially available
  - ▶ Efficiencies in the upper 90%<sub>s</sub>
  - ▶ Power densities approaching 3 kW/in<sup>3</sup>
- ▶ 2750 W/in<sup>3</sup>
  - ▶  $\approx 98\%$  efficient
  - ▶ 1750 W



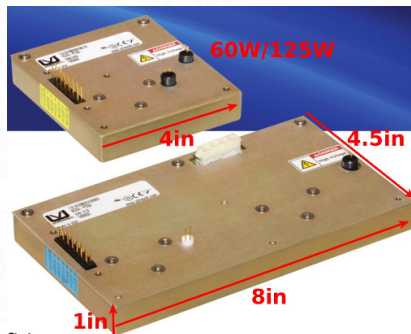
[www.vicor.com](http://www.vicor.com)

# High voltage supply development has Lagged

- ▶ High voltage power supplies remain expensive and relatively inefficient
- ▶ If fast pulses are needed a high voltage switch is generally used in conjunction with a capacitor
- ▶ Efficiencies in the 60%*s* are common
- ▶ Typical power densities  $< 10 \text{ W/in}^3$

## Ultravolt High Power C Series

- ▶  $9 \text{ W/in}^3$
- ▶ 30 V to 2000 V dc-dc

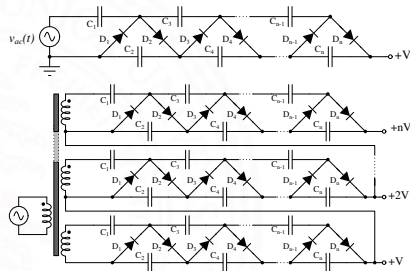


[www.ultravolt.com](http://www.ultravolt.com)

# high voltage circuits

- Various circuits can be used to generate high voltages:

- Fly-back converters
- Marx generators
- Cockcroft–Walton multiplier
- Quasi–resonant, resonant converters
- and cascaded versions of these

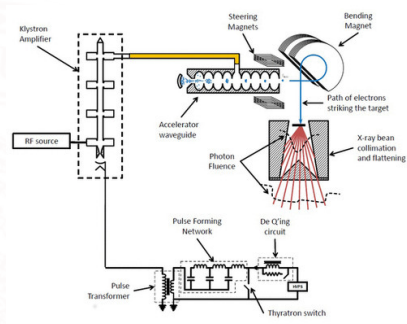


- Parasitics, output impedance, device stress, etc, impose practical limits to the number of stages that can be cascaded to produce large voltage gains
  - CockcroftWalton multiplier limited to 10-12 stages due to loading effects



# High tech applications demand innovation

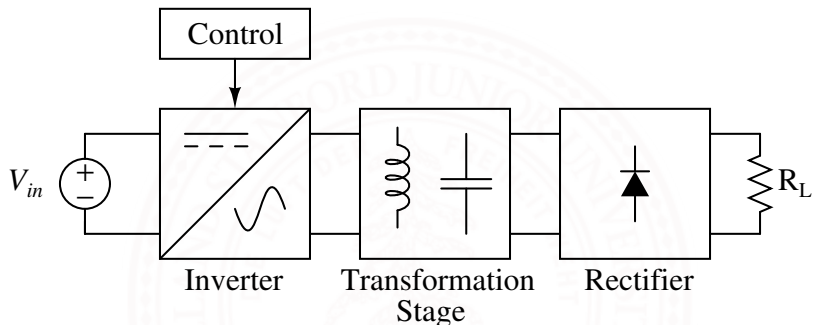
- ▶ Applications in medical, space, military, etc. require short pulses of high voltage
- ▶ Transient response of conventional supplies is typically slow



Anderson R., et. al "Simulation of a medical linear accelerator for teaching purposes" Journal of Applied Clinical Medical Physics, 2015

- ▶ Fast pulses generally require a fast high voltage switch discharging a large storage capacitor
- ▶ Charging time limits pulse duty cycle
- ▶ Energy stored within the circuit is high

# Resonant converter structure



## Inverter

Takes dc input power, deliver ac power

## Transformation stage

Provides impedance matching

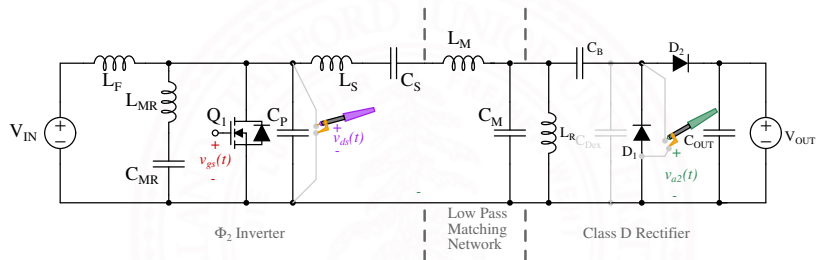
## Rectifier

Takes ac power, delivers dc power to  $R_L$

[2] J.M. Rivas, O. Leitermann, Y. Han, et al, "A very high frequency dc-dc converter based on a class  $\Phi_2$  resonant inverter," in Proc. Power Electronics Specialists Conference, 2008. pp. 1657-1666

[4] W. Liang, J. Glaser, and J. Rivas, 13.56 MHz high density dc-dc converter with PCB inductors, in Proc. 2013 Twenty-Eighth Annual IEEE Applied Power Electronics Conference and Exposition (APEC), 2013, pp. 633640.

# Previous work involving a single stage resonant design

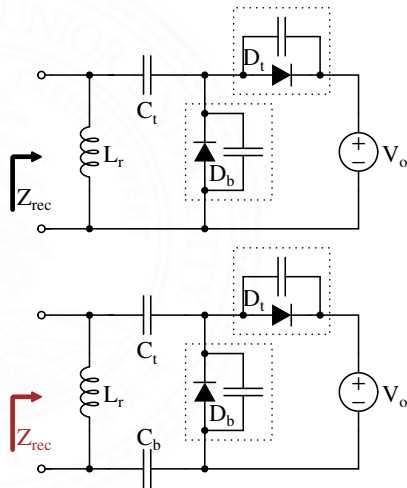


- ▶ 40 V to 500 V 27.12 MHz step up design was tested
- ▶ Output voltage limited by rectifier diode ratings
- ▶ Matching network quality factor ( $Q$ ) increases with increasing gain ratio

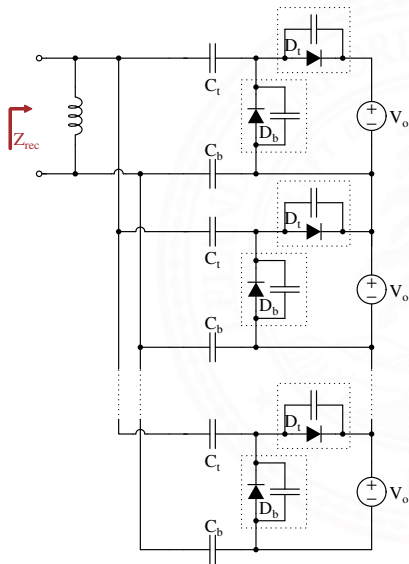
[5] Raymond, L.; Wei Liang; Jungwon Choi; Rivas, J., "27.12 MHz large voltage gain resonant converter with low voltage stress," Energy Conversion Congress and Exposition (ECCE), 2013 IEEE , vol., no., pp.1814,1821, 15-19 Sept. 2013

# Class-D rectifier modification

- ▶  $v_{\text{diode,max}} = V_{\text{OUT}}$
- ▶ Relatively low equivalent input resistance compared to related resonant rectifier topologies
- ▶ DC blocking capacitor can be split to achieve isolation

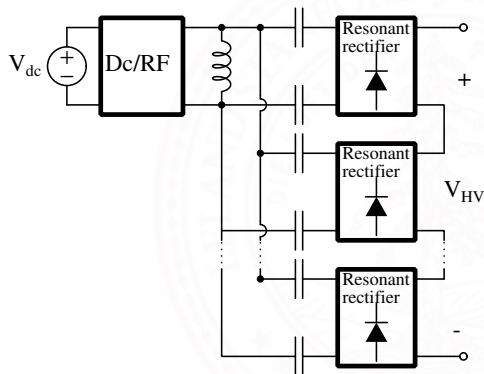


# Isolation allows for multiple rectifiers



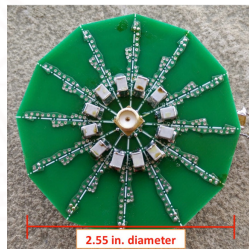
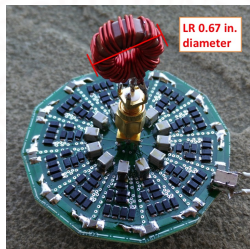
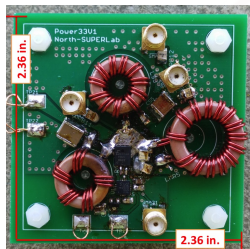
- ▶ Isolated rectifiers can be driven in parallel from a single input source
- ▶ Equivalent resistance seen by the ac source is  $R_{rect}/n$
- ▶ Outputs can be added in series to achieve voltage gain
- ▶ Elimination or reduction of matching network
- ▶  $L_R$  of each rectifier can be combined into a single inductor of value  $L_R/n$
- ▶ Overall efficiency is equal to efficiency of each individual stage

# High voltages at 10's of MHz



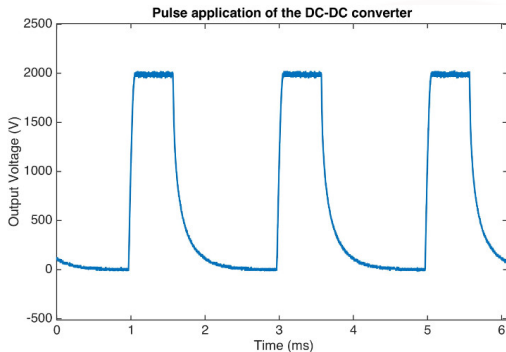
- ▶ Capacitive isolation feasible at 10's of MHz
- ▶ Cascading multiple converters for high voltage gain
- ▶ Also effective for impedance matching
- ▶ Fast pulse capability

# 12 Stage Design with Silicon



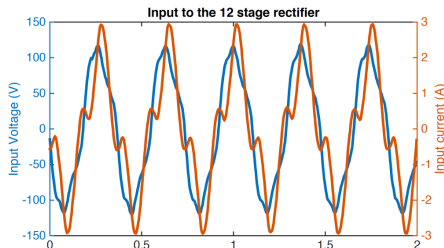
- ▶ 100 W 40 V to 2000 V dc-dc 27.12 MHz converter
- ▶ Silicon devices exhibit more ideal behavior allowing for 27.12 MHz operation
- ▶ 12 class-D stages for a voltage gain of 50 using a matching network with a quality factor of 2
- ▶ A single stage design would require a  $Q > 20$

# Power Supply Performance



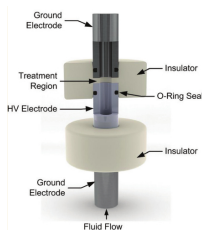
## DC-DC Performance

- ▶ 90% conversion efficiency
- ▶ Silicon diodes yield 95 % rectification efficiency as expected
- ▶ Ability to produce very square pulses

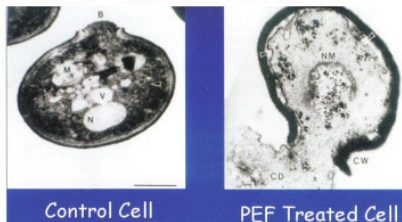




# Pulsed electric field pasteurization



Diversified Technologies Inc.



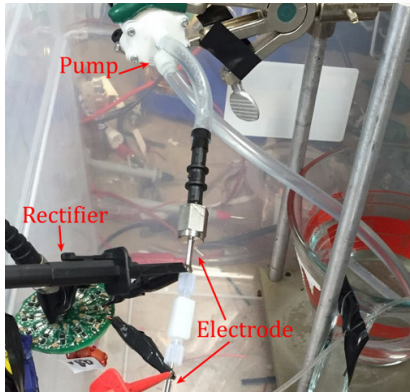
Diversified Technologies Inc.



Diversified Technologies Inc.

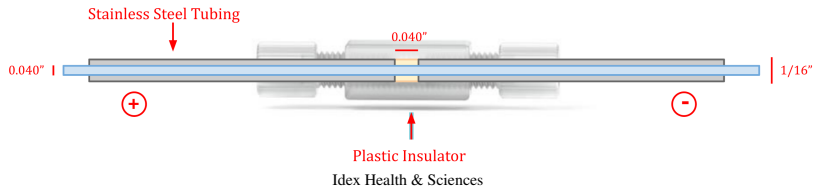
- ▶ High electric field  $\approx 20 - 50$  kV/cm pulses causes rupture bacterial membranes
  - ▶ Render bacteria un-viable
  - ▶ Non-thermal means to pasteurize foodstuffs
  - ▶ Less energy intensive than thermal pasteurization
  - ▶ Effective for pasteurization, algal oil extraction, dehydration, wastewater treatment
- ▶ Current PEF systems are costly and limited to industrial settings

# Experimental Setup

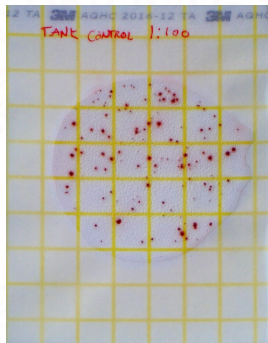
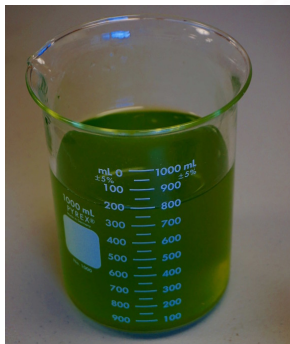


## Electrode Design for Milk and Water

- ▶ 2 kV/mm field strength
- ▶ Variable speed pump
- ▶ 50Ohm rectifier allows for remote inverter location for test purposes



# Bacteria Test Results



- ▶ Tested Effectiveness on E. Coli and Coliform
- ▶ 2-3 log reduction in measured bacteria levels
- ▶ Energy requirement of 0.5wh/L

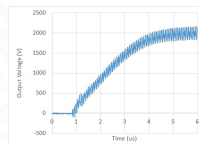
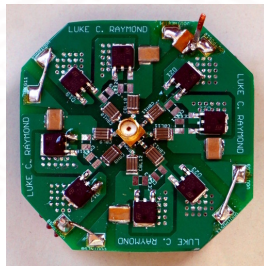
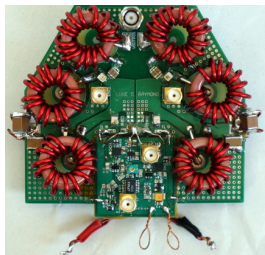
# 40% of milk in some emerging markets spoils

- ▶ Small farmers can't afford current pasteurizing equipment
- ▶ Communities rely on a network of aggregators and milk collectors to process and distribute milk
- ▶ Weather, road conditions etc., can risk milk delivery



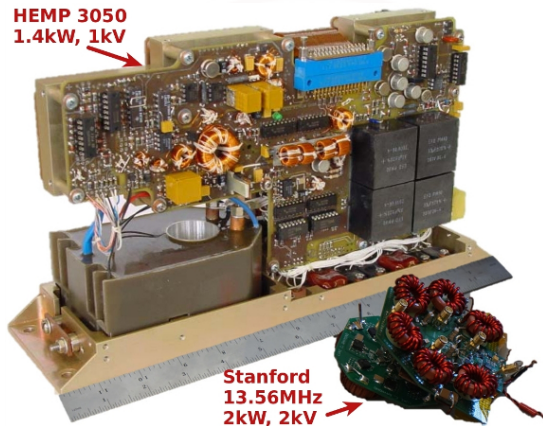
Photo credit: Nestle, Sri Lanka & Varick Schwartz, Kiva Fellow serving in Nairobi, Kenya

# 2 kW 13.56 MHz 275 V to 2 kV output isolated dc-dc



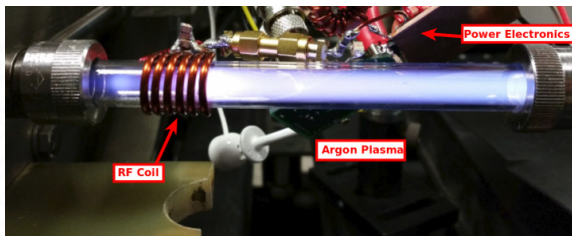
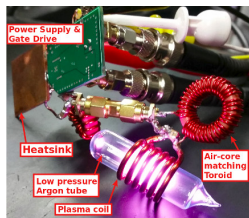
- ▶  $2 \times \Phi_2$  inverters using GaN Systems 650 V MOSFETs
- ▶ 4x500 W rectifiers with 500 V outputs in series
- ▶ 94% inverter efficiency
- ▶  $4 \mu\text{s}$  transient response
- ▶  $250 \text{ W/in}^3$  including gate drive and cold plate
- ▶ 90% rectifier efficiency vs. 97% predicted by simulation model

# HV supplies for satellite applications



- ▶ Stanford's 2 kW, 2 kV 13,56 MHz converter
  - ▶  $\approx 200 \text{ W/in}^3$
  - ▶ 5 kW/kg

# Applications: Satellite propulsion



Plasma  
Discharge  
Modes

Capacitive



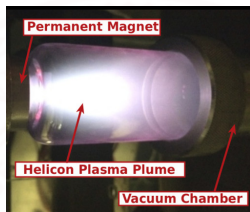
Inductive



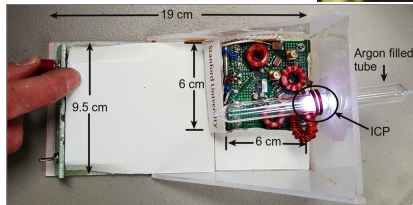
Helicon

- ▶ Miniaturized plasma sources have enormous potential for satellite propulsion
- ▶ Ion drives (RFIT, Hall Thrusters) use large PPU's
- ▶ We are collaborating with Prof. Mark Capelli to make a miniature helicon thruster for cubesats

# Miniature Helicon Thruster



Parameter	Value
Ion mean velocity:	52 km/s
Ionization fraction:	27%
Mass flow rate:	13.4 $\mu\text{g/s}$



- Preliminary measurements are very promising
- It fits in a cubesat!

*David Biggs, Sam Avery, Luke Raymond, Wei Liang, Nicolas Gascon, Juan Rivas-Davila, Mark Cappelli, "A Compact Helicon Thruster for Small Satellites" 2015 Interplanetary Small Satellite Conference, Santa Clara CA.*



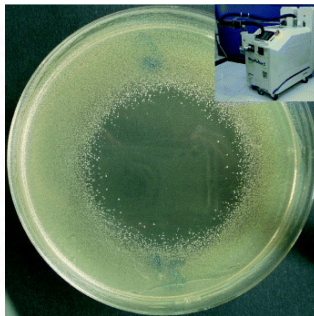
# Plasma Medicine



Max Planck Institute



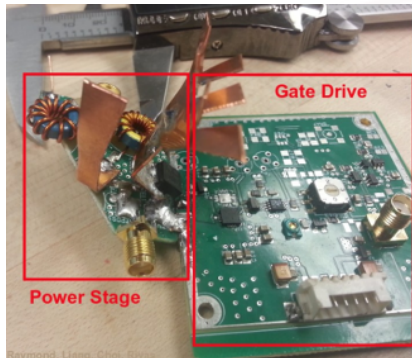
Max Planck Institute



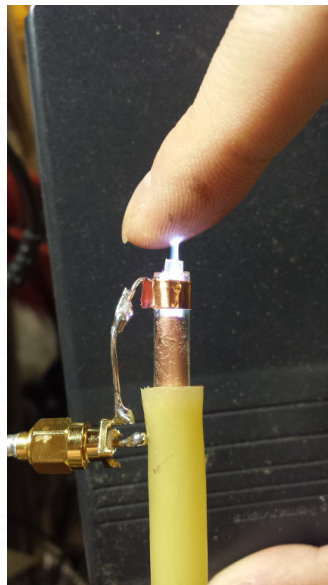
Max Planck Institute

- ▶ Plasma is effective for wound treatment and biofilm control
- ▶ Effective against MRSA and other anti-biotic resistant pathogens
- ▶ Current plasma systems are large and costly

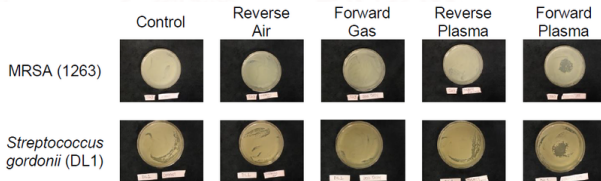
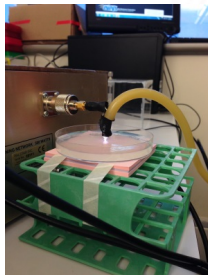
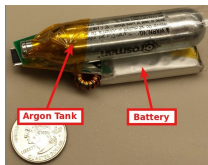
# VHF Power enables miniature plasma sources



- ▶ Miniaturized plasma generator for bio-film control
- ▶ Prototype battery operated & switching at 13.56 MHz



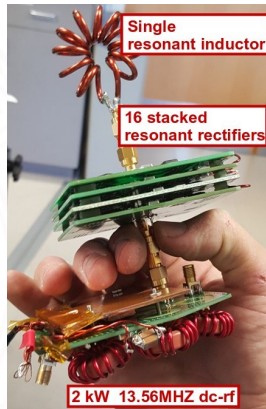
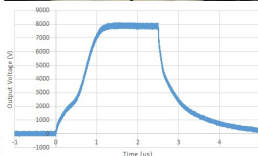
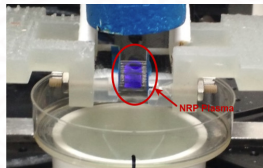
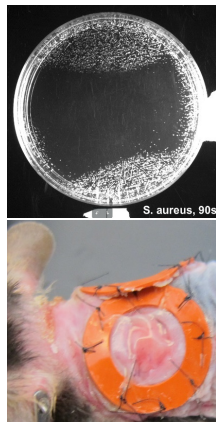
# Portable plasma source



In Collaboration with Prof. Alex Rickard (UofM)

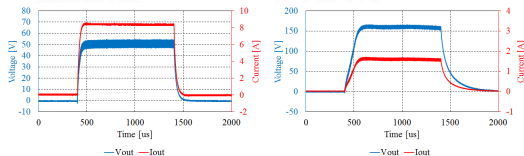
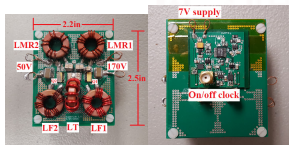
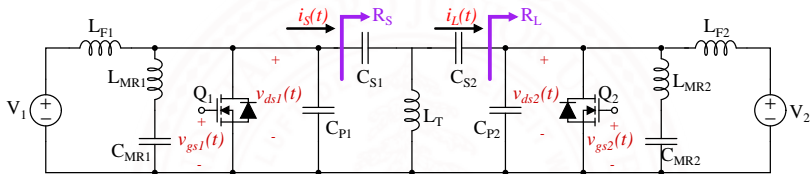
- Preliminary testing shows substantial bacterial reduction even with short pulses

# Nanosecond Repetitively Pulsed (NRP) Plasma



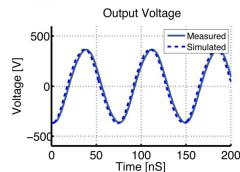
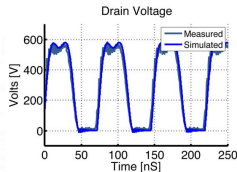
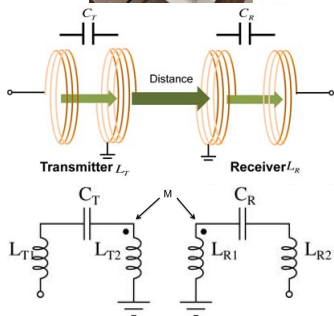
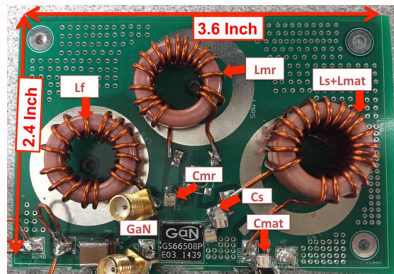
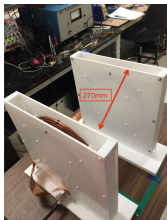
- ▶ NRP plasmas can kill biofilm and wound treatment
  - ▶ Validated in vitro and in vivo
  - ▶ Significant reduction in healing time
  - ▶ Effective on *S. aureus*, MRSA
- ▶ HF converters can reduce the size of the supply coupled to PFN

# 27.12 MHz GaN Bi-directional Resonant Power Converter



- ▶ 27.12 MHz 420 W Bidirectional dc-dc converter
- ▶  $V_{in} = 170 \text{ V}$ ,  $V_{out} = 50 \text{ V}$ ,  $\eta \approx 81\%$ , power density  $\approx 120 \text{ W/in}^3$

# Wireless power transfer at 13.56 MHz



►  $\eta=86.6\%$ ,  $P_{IN}=950\text{ W}$ ,  $P_{OUT}=823\text{ W}$   
at  $V_{IN}=200\text{ V}$  and distance=270 mm

# Acknowledgments

## Students and Collaborators

- ▶ Superlab
  - ▶ Wei Liang, Luke Raymond, Jungwon Choi, Lei Gu, (North) Kawin Surakitbovorn, Brian Holman, Gabriel Vega, Molly Dicke
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  - ▶ Prof. Capelli, David Biggs, Sam Avery, Nicolas Gascon
- ▶ Stanford Medical school
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  - ▶ Prof. Alexander Rickard, Ella Dolan

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